

Chip Schottky Barrier Diodes

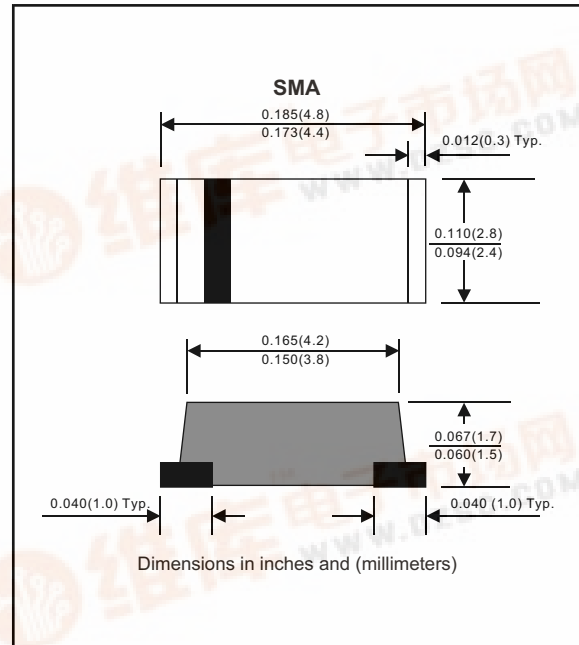
Formosa MS

FM5822-A

Silicon epitaxial planer type

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-O Utilizing Flame Retardant Epoxy Molding Compound.
- For surface mounted applications.
- Exceeds environmental standards of ML-S-19500 / 228
- Low leakage current



Mechanical data

Case : Molded plastic, JEDEC DO-214AC
 Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
 Polarity : Indicated by cathode band
 Mounting Position : Any
 Weight : 0.0015 ounce, 0.15 gram

MAXIMUM RATINGS (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.1	I_0			3.0	A
Forward voltage	$I_F = 1 \text{ A}, T_A = 25^\circ\text{C}$	V_F			0.42	V
	$I_F = 2 \text{ A}, T_A = 25^\circ\text{C}$	V_F			0.49	V
	$I_F = 1 \text{ A}, T_A = 125^\circ\text{C}$	V_F			0.34	V
	$I_F = 2 \text{ A}, T_A = 125^\circ\text{C}$	V_F			0.43	V
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC methode)	I_{FSM}			80	A
peak reverse voltage		V_{RRM}			40	V
RMS voltage		V_{RMS}			28	V
Continuous reverse voltage		V_R			40	V
Reverse current	$V_R = V_{RRM}, T_A = 25^\circ\text{C}$	I_R			0.5	mA
	$V_R = V_{RRM}, T_A = 125^\circ\text{C}$				20	mA
Thermal resistance	Junction to ambient	R_{JA}			80	$^\circ\text{C} / \text{w}$
Diode junction capacitance	f=1MHz and applied 4vDC reverse voltage	C_J		250		pF
Operating temperature		T_J	-55		+150	$^\circ\text{C}$
Storage temperature		T_{STG}	-55		+150	$^\circ\text{C}$



RATING AND CHARACTERISTIC CURVES (FM5822-A)

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

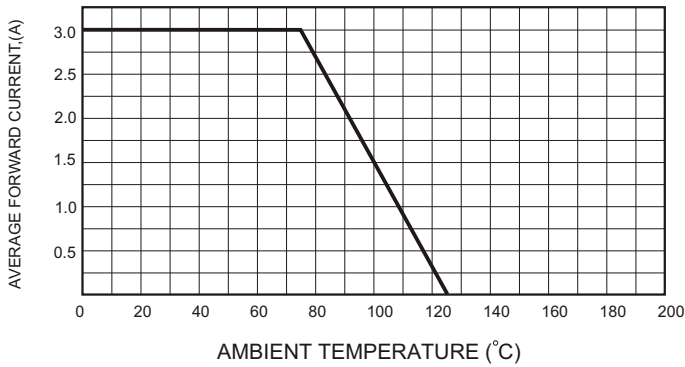


FIG.2-TYPICAL FORWARD CHARACTERISTICS

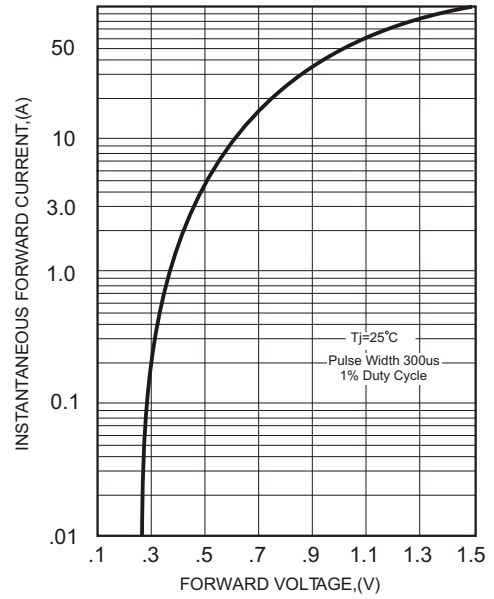


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

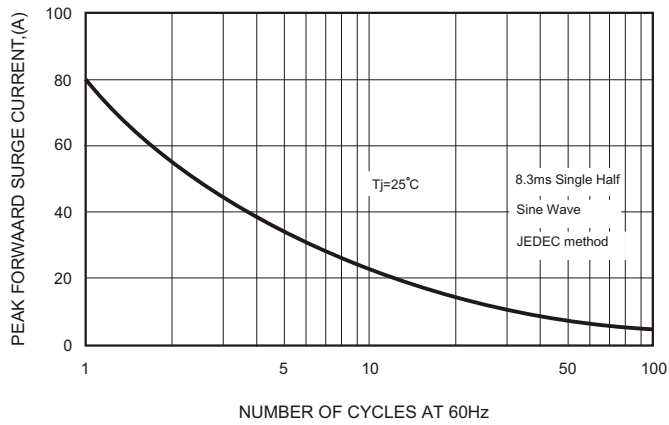


FIG.4-TYPICAL JUNCTION CAPACITANCE

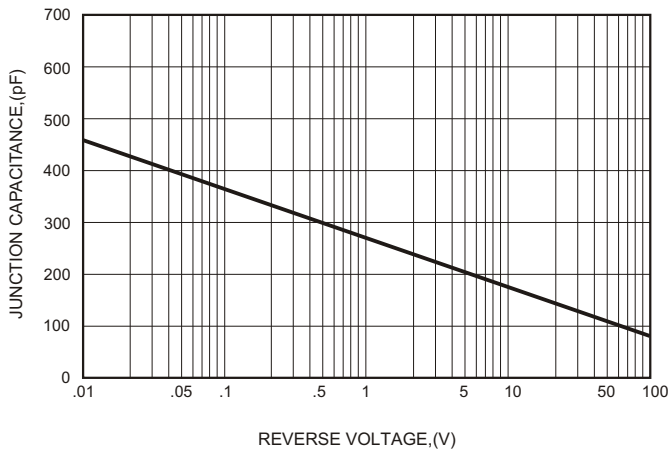


FIG.5 - TYPICAL REVERSE CHARACTERISTICS

